

# RGW80TS65EHR

650V 40A Field Stop Trench IGBT

V <sub>CES</sub>	650V
Ι <sub>C (100°C)</sub>	40A
V <sub>CE(sat) (Typ.)</sub>	1.5V
P <sub>D</sub>	214W

#### Features

- 1) AEC-Q101 Qualified
- 2) Low Collector Emitter Saturation Voltage
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating ; RoHS Compliant

#### Application

Automotive

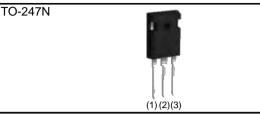
On & Off Board Chargers

DC-DC Converters

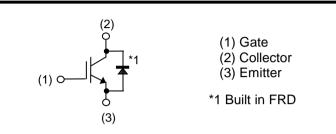
PFC

Industrial Inverter

#### Outline



#### Inner Circuit



#### Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGW80TS65E

#### •Absolute Maximum Ratings (at T<sub>c</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		V <sub>GES</sub>	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι <sub>C</sub>	80	А
Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	Ι <sub>C</sub>	48	А
Pulsed Collector Current		I <sub>CP</sub> *1	160	А
Diada Farward Current	$T_{\rm C} = 25^{\circ}{\rm C}$	١ <sub>F</sub>	73	А
Diode Forward Current	$T_{\rm C} = 100^{\circ}{\rm C}$	I <sub>F</sub>	43	А
Diode Pulsed Forward Current		I <sub>FP</sub> <sup>*1</sup>	160	А
$T_c = 25^{\circ}C$		P <sub>D</sub>	214	W
Power Dissipation	$T_{\rm C} = 100^{\circ}{\rm C}$	P <sub>D</sub>	107	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

\*1 Pulse width limited by T<sub>jmax.</sub>

#### RGW80TS65EHR

#### •Thermal Resistance

Deremeter	Symbol	Values			Linit
Parameter		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.70	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.93	°C/W

#### ●IGBT Electrical Characteristics (at T<sub>i</sub> = 25°C unless otherwise specified)

Parameter	Symbol Conditions		Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	I <sub>C</sub> = 10μΑ, V <sub>GE</sub> = 0V	650	-	-	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	-	-	10	μA
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 26.0mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_{C} = 40A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.5 1.85	1.9 -	V

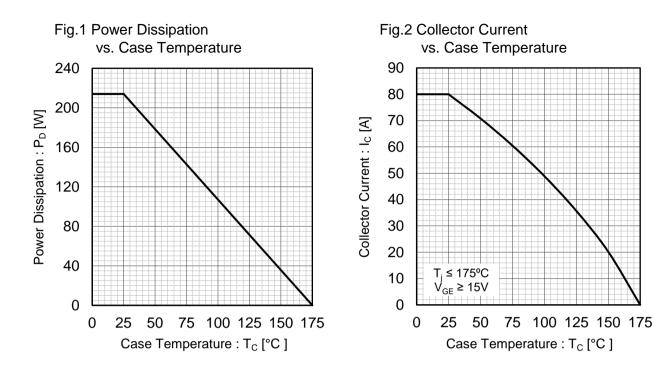
#### RGW80TS65EHR

## •IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	Symbol	Conditions		Unit			
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V,	-	3320	-		
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V,$	-	83	-	pF	
Reverse transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	60	-		
Total Gate Charge	Qg	V <sub>CE</sub> = 400V,	-	110	-		
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 40A,	-	23	-	nC	
Gate - Collector Charge	Q <sub>gc</sub>	V <sub>GE</sub> = 15V	-	41	-		
Turn - on Delay Time	t <sub>d(on)</sub>		-	43	-		
Rise Time	t <sub>r</sub>	I <sub>C</sub> = 20A, V <sub>CC</sub> = 400V, V <sub>GE</sub> = 15V, R <sub>G</sub> = 10Ω,	-	11	-	ns	
Turn - off Delay Time	t <sub>d(off)</sub>	$T_i = 25^{\circ}C$	-	148	-		
Fall Time	t <sub>f</sub>		37	-			
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> include diode reverse recovery	-	0.34	-	mJ	
Turn - off Switching Loss	E <sub>off</sub>	,	-	0.33	-	mj	
Turn - on Delay Time	t <sub>d(on)</sub>		-	39	-		
Rise Time	t <sub>r</sub>	$I_{C} = 20A, V_{CC} = 400V,$ $V_{GE} = 15V, R_{G} = 10\Omega,$	-	12	-	]	
Turn - off Delay Time	t <sub>d(off)</sub>	$T_j = 175^{\circ}C$	-	179	-	ns	
Fall Time	t <sub>f</sub>	Inductive Load	-	75	-		
Turn - on Switching Loss	Eon	*E <sub>on</sub> include diode reverse recovery	-	0.36	-	mJ	
Turn - off Switching Loss	E <sub>off</sub>		-	0.51	-	IIIJ	
Reverse Bias Safe Operating Area	RBSOA	$I_{C} = 160A, V_{CC} = 520V,$ $V_{P} = 650V, V_{GE} = 15V,$ $R_{G} = 100\Omega, T_{j} = 175^{\circ}C$	FU	ILL SQUA	RE	-	

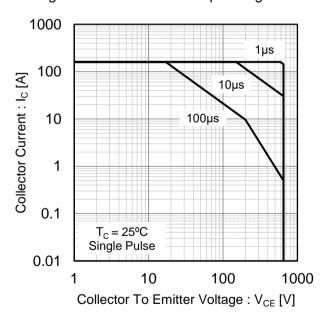
## •FRD Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

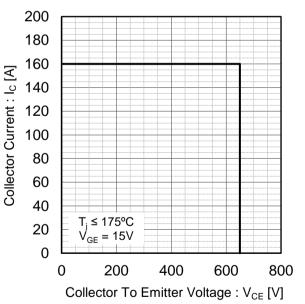
Parameter	Symbol	Conditions	Values			Linit
	Symbol		Min.	Тур.	Max.	Unit
		I <sub>F</sub> = 40A,				
Diode Forward Voltage	$V_{F}$	T <sub>j</sub> = 25°C	-	1.45	1.9	V
		T <sub>j</sub> = 175°C	-	1.55	-	
Diode Reverse Recovery Time	t <sub>rr</sub>		-	86	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>	I <sub>F</sub> = 20A, V <sub>CC</sub> = 400V,	-	7.2	-	A
Diode Reverse Recovery Charge	Q <sub>rr</sub>	di <sub>F</sub> /dt = 200A/µs, T <sub>j</sub> = 25°C	-	0.33	-	μC
Diode Reverse Recovery Energy	Err		-	10.0	-	μJ
Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20A, V <sub>CC</sub> = 400V, di <sub>F</sub> /dt = 200A/µs, T <sub>j</sub> = 175°C	-	147	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>		-	9.7	-	A
Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	0.83	-	μC
Diode Reverse Recovery Energy	E <sub>rr</sub>		-	36.3	-	μJ



### Fig.3 Forward Bias Safe Operating Area







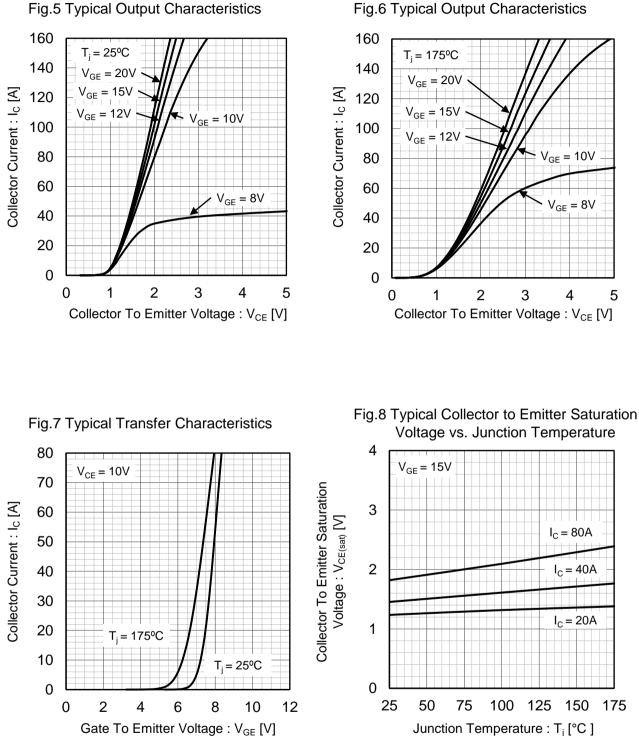
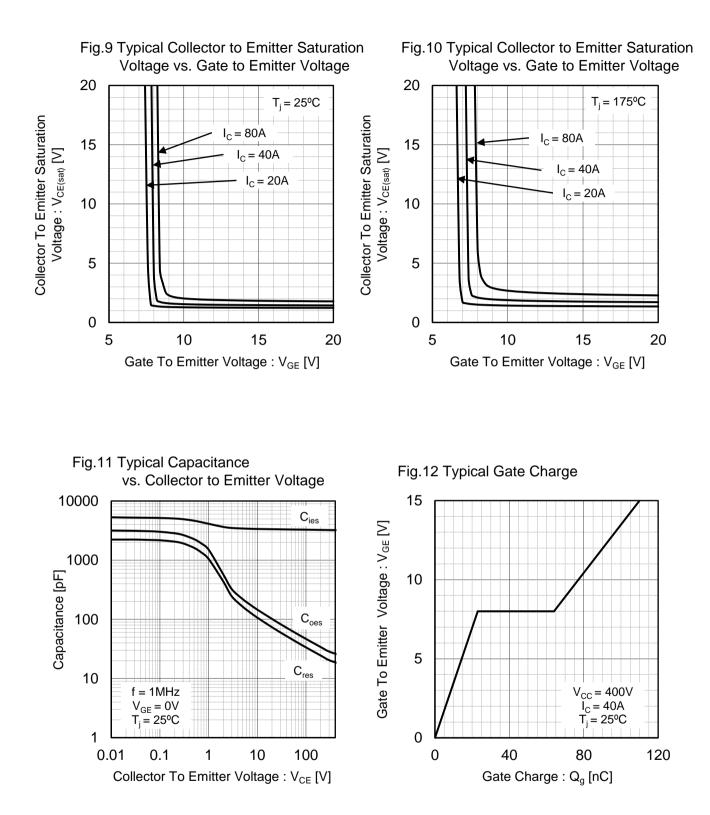
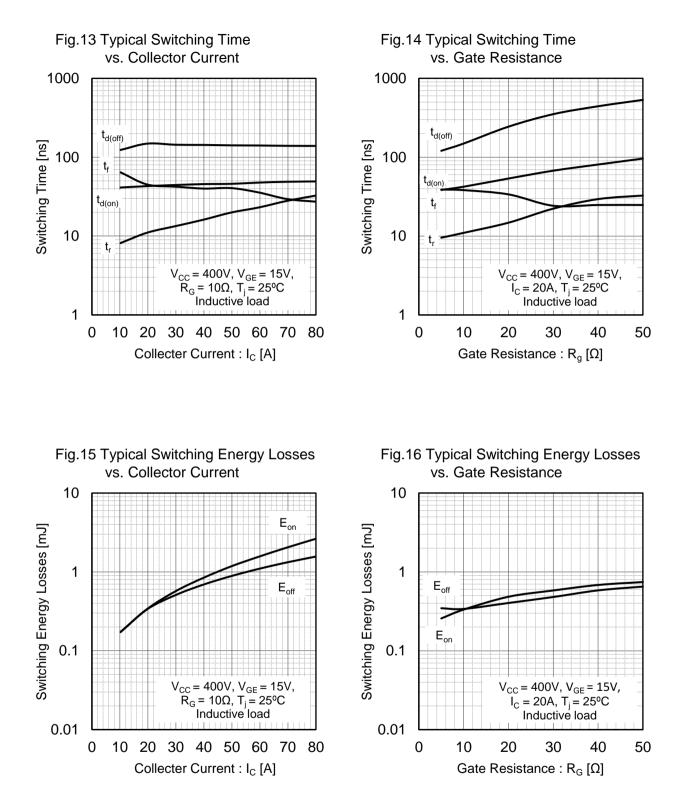
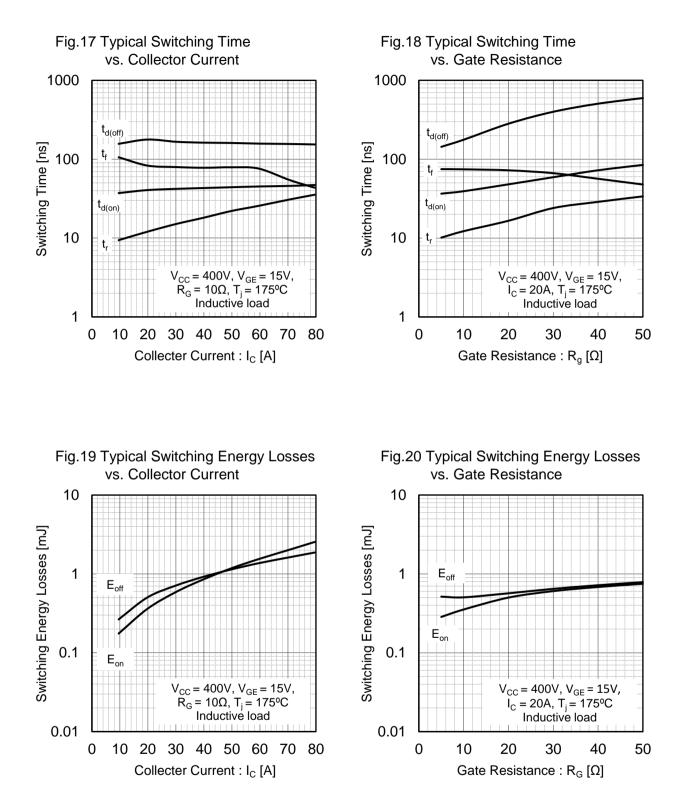
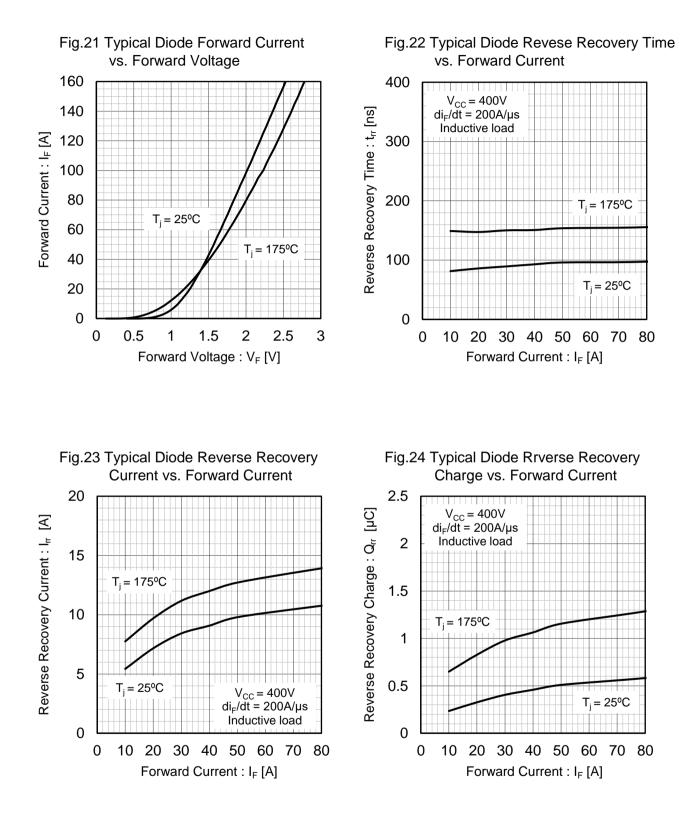


Fig.6 Typical Output Characteristics









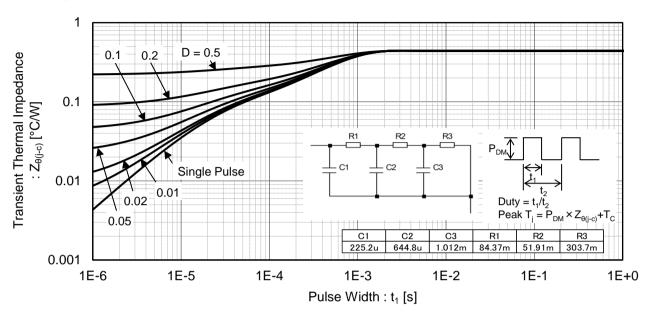
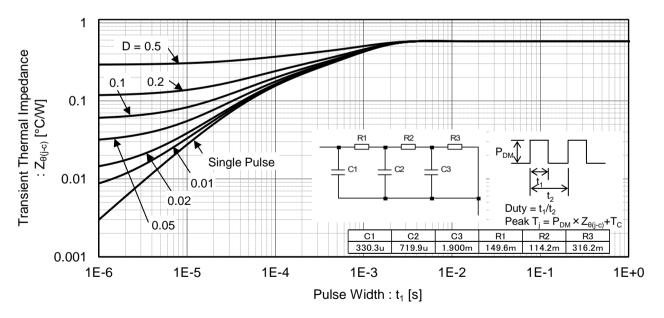


Fig.25 Typical IGBT Transient Thermal Impedance

Fig.26 Typical Diode Transient Thermal Impedance



#### Inductive Load Switching Circuit and Waveform

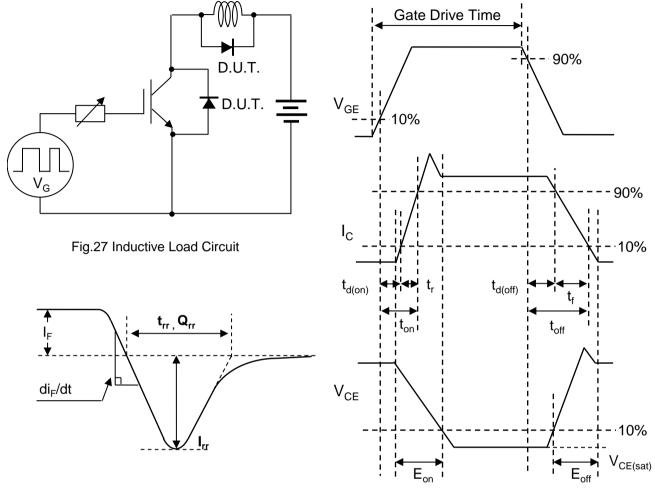


Fig.29 Diode Reverse Recovery Waveform

Fig.28 Inductive Load Waveform



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